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	ial.
Inclosure Mater Metal	
Overall Length:	
	nches and 0.260 inches
Terminal Lengt	
-	nches and 1.750 inches
Overall Diamete	
	nches and 0.370 inches
Internal Configu	
Junction contact	
	nally-electrically Connected To Case:
Anode	
Mounting Metho	ad.
Terminal	
Terminal Circle	Diameter:
0.200 inches	
Semiconductor	Material
Silicon	
	In Volts Per Characteristic:
	oltage, peak and 150.0 nonrepetitive peak reverse voltage, peak total value
	Per Characteristic:
-	rward current, total rms megahertz and 15.00 amperes forward current, average preset
	ating Tempurature Per Measurement Point:
	elsius ambient air
Special Feature	
•	arrangement: pnpn
•	al And Location:
Terminal surface	
Precious Materi	
Gold	
Test Data Docu	ment:
81349-mil-s-195 ⁴	00 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes	s commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental ar	nd performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type	And Quantity:
3 uninsulated wir	re lead
Specification Da	ata:
81349-mil-s-195	00/276 government specification
Shelf Life:	
N/a	
Unit Of Measure	2:
Demilitarization	c.
No	

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